## RA-0025



- InGaAs PIN/TIA
- 155 Mb/s
- Differential output and AGC

**Performance Highlights** 

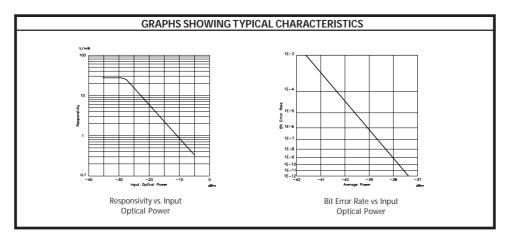
- Responsivity typically 27 V/mWTypical sensitivity -37dBm
- Overload -5dBm

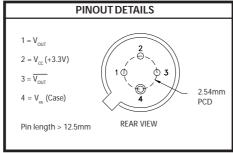
LIMITING VALUES	SYMBOL	VALUE	UNITS
Supply voltage	V <sub>DD</sub>	+3.8	V
Operating temperature	$T_{amb}$	-20 to +70	°C
Storage temperature	$T_{stg}$	-40 to +85	°C

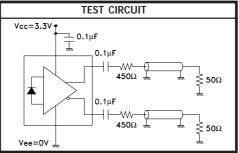
OPTICAL/ELECTRICAL CHARACTERISTICS	SYMBOL	MIN	ТҮР	MAX	UNITS	TEST CONDITION
Responsivity	R		27		V/mW	P <sub>IN</sub> = -30dBm, single ended
Operating wavelength	λ	1270		1560	nm	
Rise and Fall time (20 - 80%)	t <sub>f</sub>		2.0		ns	$P_{IN} = -30dBm$
Bandwidth	f <sub>c</sub>		150		MHz	$P_{IN} = -30dBm$
Low frequency cutoff	f <sub>L</sub>		15		kHz	
Output offset voltage	V <sub>off</sub>	1.5			V	Dark state, R <sub>L</sub> = ∞
Optical overload	P <sub>o L</sub>	-5.5	-5		dBm	
Optical sensitivity	P <sub>M IN</sub>	-35	-37		dBm	
Supply current	I <sub>s</sub>		25		mA	Dark state, R <sub>L</sub> = ∞
Operating voltage	V <sub>c c</sub>	-0.3	3.3	3.8	V	

**Unless otherwise specified:**  $T_{amb} = 25^{\circ}C$ , Vcc = 3.3V, Vee = 0V,  $R_{L} = 500\Omega$  (coupled through capacitors),  $\lambda = 1310$ nm **Note:** The amp is designed to drive a load  $>499\Omega$  and can not drive a  $50\Omega$  load









## **NOTES:**

1) The device is very susceptible to damage by electrostatic discharge.